



Supplementary Materials

Direct Growth of Patterned Vertical Graphene Using Stress Mismatch between Sacrificial Layer and Substrate

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Table S1. Physical and mechanical properties used in the simulation of stress distribution.

		Thermal conductivity		CTE		Elastic modulus		Poisson's ratio		References
		T (°C)	λ (W/m·K)	T (°C)	α (10 ⁻⁶ /K)	T (°C)	E (GPa)	T (°C)	ν	
Si		20	139.4	27	2.59	25	168.1			
		200	82.4	127	3.2	100	167.6			
		400	50.3	227	3.59	200	166.6			
		600	36.7	327	3.83	300	164.8	27	0.278	[42-45]
		800	27.4	427	3.99	400	163.2			
		1000	23.7	527	4.1	500	162.4			
SiO ₂		27	1.3	0	0.4	0	71.8			
				100	0.62	100	71.4			
				200	0.75	200	70.8			
				300	0.7	300	70.5	27	0.19	[46-49]
				400	0.65	400	70.2			
				500	0.6	500	70.1			
Cr				600	0.5	600	70.05			
				27	93	127	8.12	27	275	
				127	91.8	227	9	77	274	
				227	87.7	327	9.58	127	273	
				327	83.3	427	10.1	177	272	
				427	78.8	527	10.8	227	270	27
				527	74.9	627	11.3	277	268	0.21
				627	71.8	727	11.8	327	265	[50-53]
VG				727	69.6	827	12.2	377	262	
						927	12.7			
				27	2000					
				127	1200	27	-1.1	27	49	
				227	1010	100	-0.4	200	50	
				327	900	200	0.5	400	51	
				427	690	300	1.4	600	53	27
				527	600	400	2.3	800	55	0.16

627	510	500	3.3	1000	61
727	500				

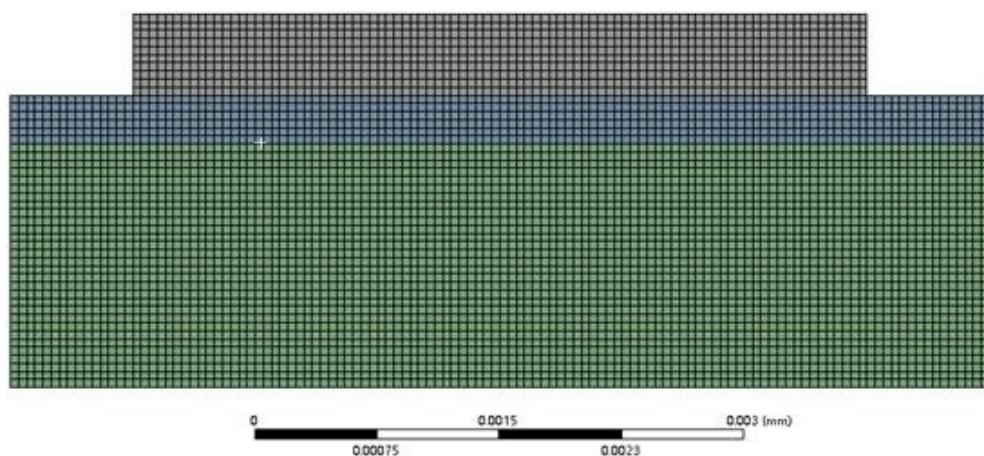


Figure S1. FE model for thermal stress analysis of a SiO₂/Si substrate with patterned Cr film (before VG synthesis).

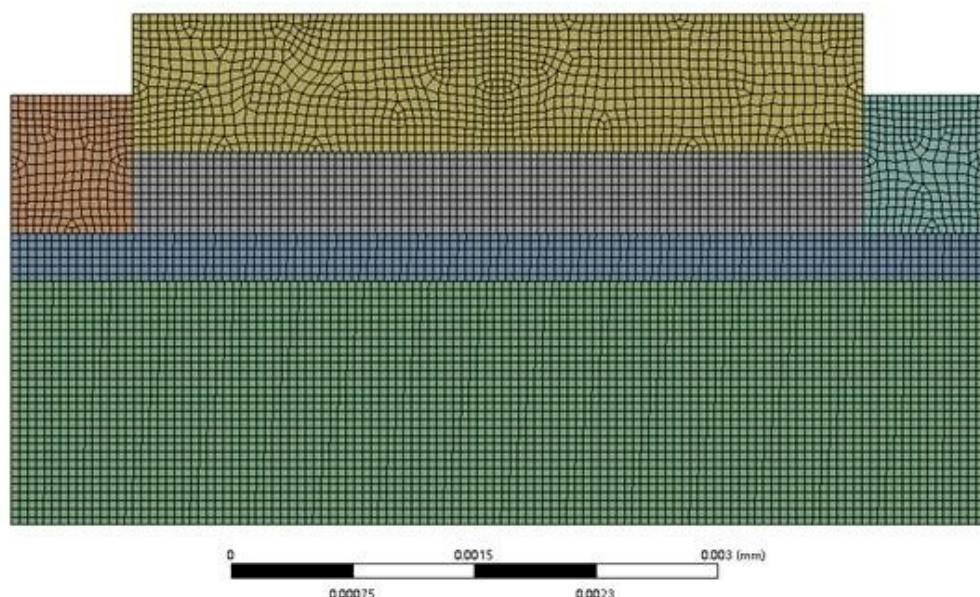


Figure S2. FE model for thermal stress analysis of a SiO₂/Si substrate with VG and patterned Cr film (after VG synthesis).

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